

The Conference Theme

"Emerging Topics and Advanced Electronics"

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Opening

9:15-9:20 Opening Remarks by M. Kimura (Ryukoku University)

9:20-9:50 Poster Short Presentation

Keynote Speech-I

Energy Harvesting and Energy Saving

9:50-10:50

K-1 Nanostructure Thermoelectrics Yoshiaki Nakamura (Osaka University)

10:50-11:10 Authors' Interview & Break

General Session -Circuits and Sensors-

11:10-11:30

G-1 Enhanced Mobile Robot Localization with Lidar and IMU Sensor
Darren Ren-Yee Phang and Wai-Kong Lee (Universiti Tunku Abdul Rahman)
Nobuto Matsuhira (Shibaura Institute of Technology)
Michail Papoutsidakis (University of West Attica)

11:30-11:50 (Withdraw)

G-2 Standalone Solar PV Maximum Power Point Tracking Using Interval Type-2 Fuzzy

Logic

Angelo A. Beltran Jr. (Adamson University)

11:50-12:10

G-3 Recent Design Techniques for Improving Sensing Accuracy of Oscillator-based Sensor Interfaces in Standard CMOS Process
Wei Zhou, Wang Ling Goh (Nanyang Technological University)
Yuan Gao (Agency for Science, Technology and Research)

12:10-13:40 Lunch

Energy Harvesting and Energy Saving

13:40-14-10 (Invited)

E-1 Possibility of Dye-Sensitized Solar Cell as Energy Harvester Atsushi Fukui (Sharp Corp.)

14:10-14-40 (Invited)

E-2 Polymer Light-Emitting Devices with Selectively Transparent Photonic Crystals Consisting of Printed Inorganic/Organic Hybrid Dielectric Films Hirotake Kajii (Osaka University)

14:40-15:10 (invited)

E-3 Solid-State Lithium Thin-Film Batteries Capable of Fast Charging Taro Hitosugi (Tokyo Institute of Technology)

15:10-15:30 Authors' Interview

Break (15:30-15:50)

Keynote Speech-II

Artificial Intelligence and Related Technology

15:50-16-50

K-2 Physical Reservoir Computing Devices and Complex-Valued Neural Networks Akira Hirose, Ryosho Nakane, Gouhei Tanaka (University of Tokyo)

16:50-17:10 Authors' Interview

Closing

[17:10 - 17:40 Award Committee]

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9:15-10:40 Poster Presentation

Special Session on Industry Activity

-Analysis, Material & Process Technology-

10:45-11:05 (Invited)

S-1 Sub-Gap Defect States in Back-Channel-Etched Amorphous In-Ga-Zn-O TFTs Studied by Photoinduced Transient Spectroscopy Kazushi Hayashi and Mototaka Ochi (Kobe Steel, Ltd.)

11:05-11:25 (Invited)

S-2 High Reliability InGaZnO TFT by Inductively Coupled Plasma Sputtering System Daisuke Matsuo, Ikeda Takuya, Shigeaki Kishida, Yoshitaka Setoguchi, And Yasunori Andoh (Nissin Electric Co., Ltd.)
Ryoko Miyanaga, Mami N. Fujii, Yukiharu Uraoka (NAIST)

11:25-11:45 (Invited)

S-3 Industrial Device Manufacturing Process Technologies toward the Future Masahiko Tanaka (SPP Technologies Co., Ltd.)

11:45-12:05 (Invited)

S-4 The Recent Resolution and Detection Limit Improvement of EDS and EBSD with SEM
Hirobumi Morita, Sam Marks, and Iain Anderson (Oxford Instruments)

12:05-14:15 Lunch

General Session - Materials and Devices-

14:15-14:35

G-4 Defect Evaluation of O_2 -annealed TaO_x for Transparent ReRAM with High Resistance Ratio ($R_{HRS}/R_{LRS} > 10^9$)
Soshun Doko, Yoriko Suda, Yoshiaki Ishii, and Masahiro Moniwa (Tokyo University of Technology)

14:35-14:55

G-5 Impact of SiN Capping during Ohmic Annealing on Performance of GaN-Based MISHEMTs
Shan Low, Shinsaku Kawabata, Joel Asubar, Hirokuni Tokuda and Masaaki Kuzuhara (University of Fukui)

14:55-15:15

G-6 Microstructures of ε-Ga₂O₃ Thin Film on (100) TiO₂ Substrate by Mist Chemical Vapor Deposition

Break (15:15-15:30)

15:30-17:00 Power Devices, Materials and Analysis

15:30-16:00 (Invited)

P-1 Limiting Factors of Inversion Layer Mobility in Si-Face 4H-SiC MOSFETs Munetaka Noguchi (Mitsubishi Electric)

16:00-16:30 (Invited)

P-2 Analysis and detection of dislocations in GaN Yukari Ishikawa (JFCC)

16:30-17:00 (Invited)

P-3 Process and Characterization of Vertical Ga₂O₃ Transistors Masataka Higashiwaki (NICT)

17:00-17:20 Authors' interview & Break

[Award Committee]

Awards & Closing Remark

17:25-17:45 Award Presentation M. Yoshimoto (KIT) 17:45-17:50 Closing Remark M. Yoshimoto (KIT)

Poster Papers

- PP-1. Effects of UV-LED Irradiation Towards Leaf-Lettuce Roots in Plant Factory Mitsuhiro Urano and Keisuke Uenishi (Osaka University)
- PP-2. Rapid Growth of Lettuce in Plant Factory with Sun Light and Night LED Lighting Iori Yamada and Akira Takahashi (National Institute of Technology, Nara College)
- PP-3. In-vitro experiments of artificial retina using TFTs and TFPTs Kohei Toyoda, Keisuke Tomioka, Keigo Misawa, Naoya, Naitou, and Mutsumi Kimura (Ryukoku University)
- PP-4. Ga-Sn-O TFT Fabricated with Al₂O₃ Insulating Film Kazuki Hattori, Kenta Tanino, Mutsumi Kimura, and Tokiyoshi Matsuda (Ryukoku University)
- PP-5. Growth of α- and ε-Ga₂O₃ Epitaxial Thin Films on LiTaO₃ Substrate Kazuki Shimazoe, Hiroyuki Nishinaka, Daisuke Tahara, Yuta Arata, and Masahiro Yoshimoto (Kyoto Institute of Technology)
- PP-6. Fabrication of Flexible and Epitaxial Metastable Ga₂O₃ Thin Films on Synthetic Mica Using Oxide Buffer Layer
 Yuta Arata, Hiroyuki Nishinaka, Daisuke Tahara, Kazuki Shimazoe, Yusuke Ito, and Masahiro Yoshimoto (Kyoto Institute of Technology)
- PP-7. Crystal Growth of (Bi, La)₄Ti₃O₁₂ Using a Two Step Deposition Process Homare Yoshida, Yuta Miyabe, and Mutsumi Kimura (Ryukoku University)
- PP-8. A New Temperature-Stabilized Biosensor System for Phospholipid-Immobilized Cantilever Sensor to Detect Biomaker Amyloid Protein for Parkinson Disease Ryoko Kobayashi, Minoru Noda (Kyoto Institute of Technology)

 Masanori Sawamura, Hodaka Yamakado (Kyoto University)

 Masayuki Sohgawa (Niigata University)
- PP.-9. Synapse Elements in Neural Network Based on Multilayer Cross-Point Device Using IGZO

Takumi Tsuno, Jumpei Shimura, Atsushi Kondo, and Mutsumi Kimura (Ryukoku University)

- PP-10. Ga-Sn-O Thin Film Synapse for Neural Network
 Yuki Shibayama, Daiki Yamakawa, Yuki Onishi, and Mutsumi Kimura
 (Ryukoku University)
 Hiroki Yamane, Yasuhiko Nakashima (Nara Institute of Science and Technology)
- PP-11. Optical and Electrical Properties of Si Nanowire for Si Solar Cells Masaya Kuriyama, Hidenobu Mori, and Haruhiko Yoshida (University of Hyogo)

- PP-12. Sub-Micron Gate Fabrication Process for AlGaN/GaN HEMTs Ali Baratov, Takashi Ozawa, Joel T. Asubar, Hirokuni Tokuda, and Masaaki Kuzuhara (University of Fukui)
- PP-13. Study on Luminescence and Leakage Current of AlGaN/GaN HEMTs Biased near Off-State Breakdown Shunsuke Kamiya, Takashi Nishitani, Joel T. Asubar, Hirokuni Tokuda, and Masaaki Kuzuhara (University of Fukui)
- PP-14. The Impact of Doping Concentration on the Electrical Characteristics of Z2-FET Yu Yabuuchi, Shingo Sato (Kansai University)
 Yasuhisa Omura (Academic Collaboration Associate)
- PP-15. Simulation of Optical Gain in Semiconductor Laser Structure with h-BCN Active Layer

 Daisuke Maki, Matsuto Ogawa, and Satofumi Souma (Kobe University)
- PP-16. Simulation of Graphene FET Gated by Ionic Liquid Koki Arihori, Matsuto Ogawa and Satofumi Souma (Kobe University) Junko Sato-Iwanaga (Panasonic Corporation)
- PP-17. In-Ga-Zn-O Film Thickness Dependence of Memristor Characteristic for Resistive Random Access Memory Kaito Hashimoto, Ayata Kurasaki, Mutsumi Kimura, and Tokiyoshi Matsuda (Ryukoku University)
- PP-18. Characterization and Reduction of the Tail States in GaAsBi Alloy Sho Hasegawa, Kakuyama Kyohei, Hiroyuki Nishinaka, and Masahiro Yoshimoto (Kyoto Institute of Technology)